



採購規範書

品名：氮化鎵功率元件客製化製程
案號：A512003867

目 錄

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撰寫人：_____姚寶琪_____日 期：_____2026/08/13_____

◇ 規格/功能需求：

1. 光罩14
2. GaN-on-GaN MOSFET 破片製程代工：18 pcs
- 3.

Process	Conditions		Spec
Mesa depth	Mesa etching	2.5 um	CD=5 um±5% , 75° taper Depth 1 um ±1%
Trench depth	Trench etching	1.6 um	CD=5 um±2% 75° taper Depth 1.5~2 um ±1%
Gate oxide	SiO ₂	100 nm	THK ±1%
Source metal	Ti/Al/Ni/Au	20/120/50/400 nm	R < 10 ohm
Gate metal	Ti/Au	50/400 nm	-

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